

$V_{RRM} = 5500 \text{ V}$
 $I_{F(AV)M} = 635 \text{ A}$
 $I_{FSM} = 15.5 \cdot 10^3 \text{ A}$
 $V_{F0} = 2.9 \text{ V}$
 $r_F = 1.9 \text{ m}\Omega$
 $V_{DC-Link} = 3300 \text{ V}$

Fast Recovery Diode

5SDF 08H6005

Doc. No. 5SYA1116-02 Apr. 16

- Patented free-floating technology
- Industry standard housing
- Cosmic radiation withstand rating
- Low on-state and switching losses
- Optimized for snubberless operation

Blocking

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	5SDF 08H6005	Unit
Repetitive peak reverse voltage	V_{RRM}	$f = 50 \text{ Hz}$, $t_p = 10 \text{ ms}$, $T_{vj} = 115 \text{ °C}$	5500	V
Permanent DC voltage for 100 FIT failure rate	$V_{DC-link}$	Ambient cosmic radiation at sea level in 100% Duty	3300	V
		5% Duty	3900	

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse leakage current	I_{RRM}	V_{RRM} , $T_{vj} = 115 \text{ °C}$			30	mA

Mechanical data

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_M		36	40	46	kN
Acceleration	a	Device unclamped			50	m/s ²
Acceleration	a	Device clamped			200	m/s ²

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m				0.83	kg
Housing thickness	H	$F_M = 40 \text{ kN}$, $T_a = 25 \text{ °C}$	26.2		26.6	mm
Surface creepage distance	D_S		30			mm
Air strike distance	D_a		20			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

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On-state

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Average on-state current	$I_{F(AV)M}$	Half sine wave, $T_c = 70\text{ °C}$			635	A
RMS on-state current	$I_{F(RMS)}$				1000	A
Peak non-repetitive surge current	I_{FSM}	$t_p = 10\text{ ms}$, $T_{vj} = 115\text{ °C}$, sine half wave, $V_R = 0\text{ V}$, after surge			$15.5 \cdot 10^3$	A
Limiting load integral	I^2t				$1.2 \cdot 10^6$	A ² s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_F	$I_F = 1800\text{ A}$, $T_{vj} = 115\text{ °C}$			6.3	V
Threshold voltage	V_{F0}	400...2500, $T_{vj} = 115\text{ °C}$			2.9	V
Slope resistance	r_F				1.9	mΩ

Turn-on

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Peak forward recovery voltage	V_{FRM}	$di_F/dt = 1000\text{ A/μs}$, $T_{vj} = 115\text{ °C}$			230	V

Turn-off

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. decay rate of on-state current	di/dt_{crit}	$I_{FM} = 1800\text{ A}$, $T_{vj} = 115\text{ °C}$, $V_{DC-Link} = 3300\text{ V}$			440	A/μs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse recovery charge	Q_{rr}	$I_{FQ} = 1800\text{ A}$, $V_{DC-Link} = 3300\text{ V}$, $-di_F/dt = 440\text{ A/μs}$, $L_{CL} = 300\text{ nH}$, $C_{CL} = 10\text{ μF}$, $R_{CL} = 0.65\text{ Ω}$, $D_{CL} = 5SDF\ 08H6005$, $T_{vj} = 115\text{ °C}$			3000	μAs
Reverse recovery current	I_{RM}				900	A
Turn-off energy	E_{rr}				6.5	J

Thermal

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	T_{vj}		-40		115	°C
Storage temperature range	T_{stg}		-40		125	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	$R_{th(j-c)}$	Double-side cooled $F_m = 36... 46 \text{ kN}$			12	K/kW
	$R_{th(j-c)A}$	Anode-side cooled $F_m = 36... 46 \text{ kN}$			24	K/kW
	$R_{th(j-c)C}$	Cathode-side cooled $F_m = 36... 46 \text{ kN}$			24	K/kW
Thermal resistance case to heatsink	$R_{th(c-h)}$	Double-side cooled $F_m = 36... 46 \text{ kN}$			3	K/kW
	$R_{th(c-h)}$	Single-side cooled $F_m = 36... 46 \text{ kN}$			6	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

i	1	2	3	4
R_i (K/kW)	7.713	2.766	1.044	0.480
τ_i (s)	0.5316	0.0668	0.0078	0.0020

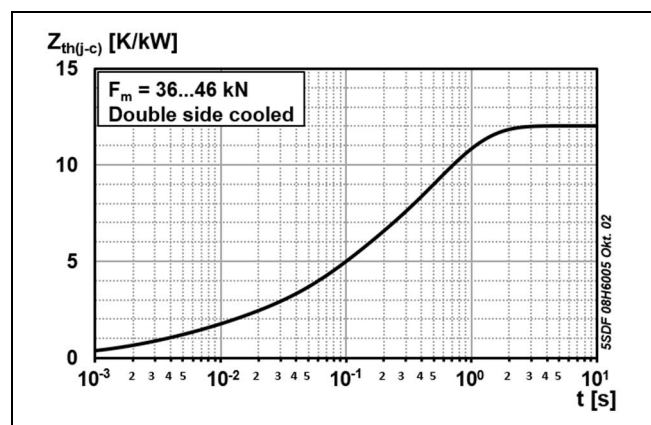


Fig. 1 Transient thermal impedance (junction-to-case) vs. time

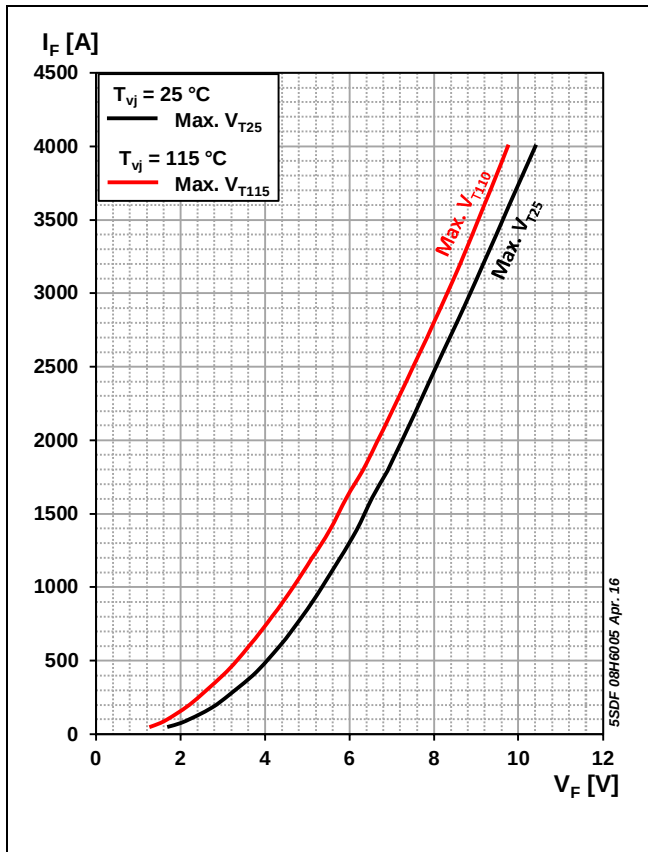


Fig. 2 On-state voltage characteristics

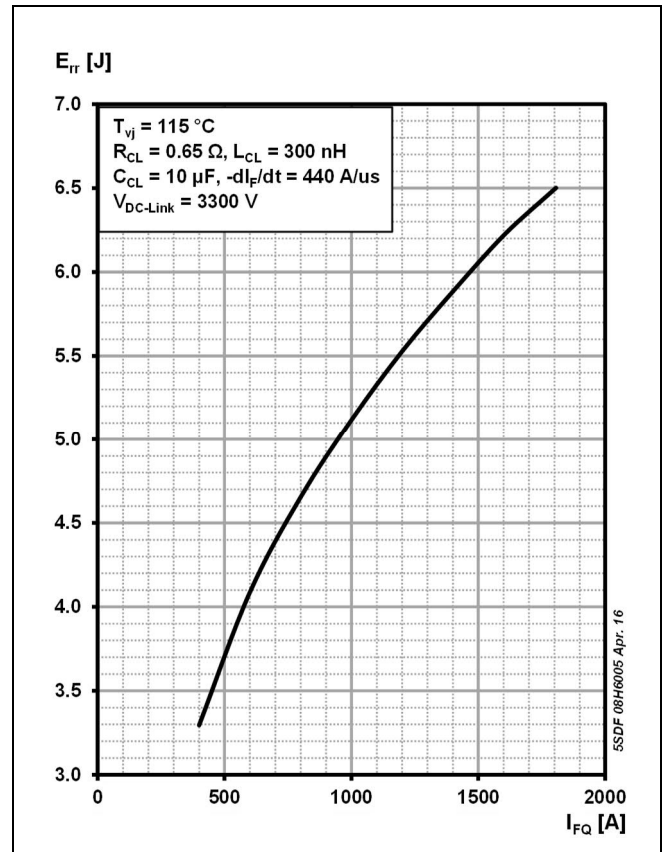


Fig. 3 Diode turn-off energy per pulse vs. turn-off current

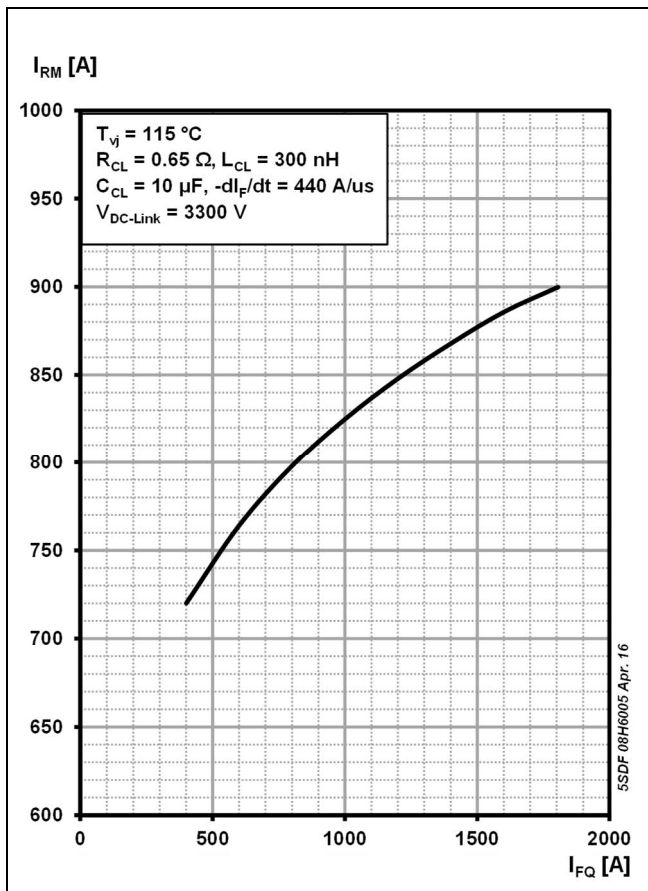


Fig. 4 Diode reverse recovery current vs. turn-off current

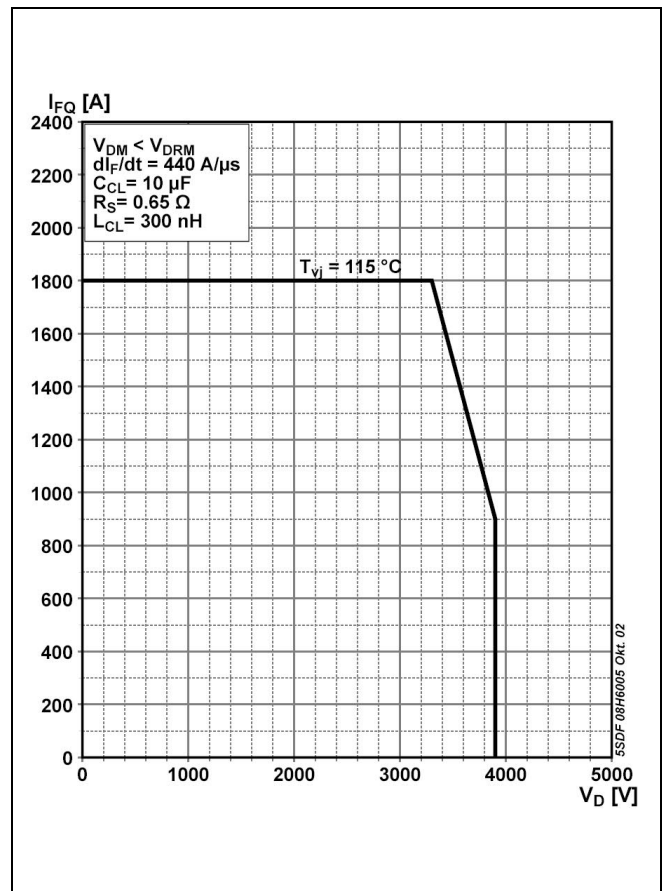


Fig. 5 Diode Safe Operating Area

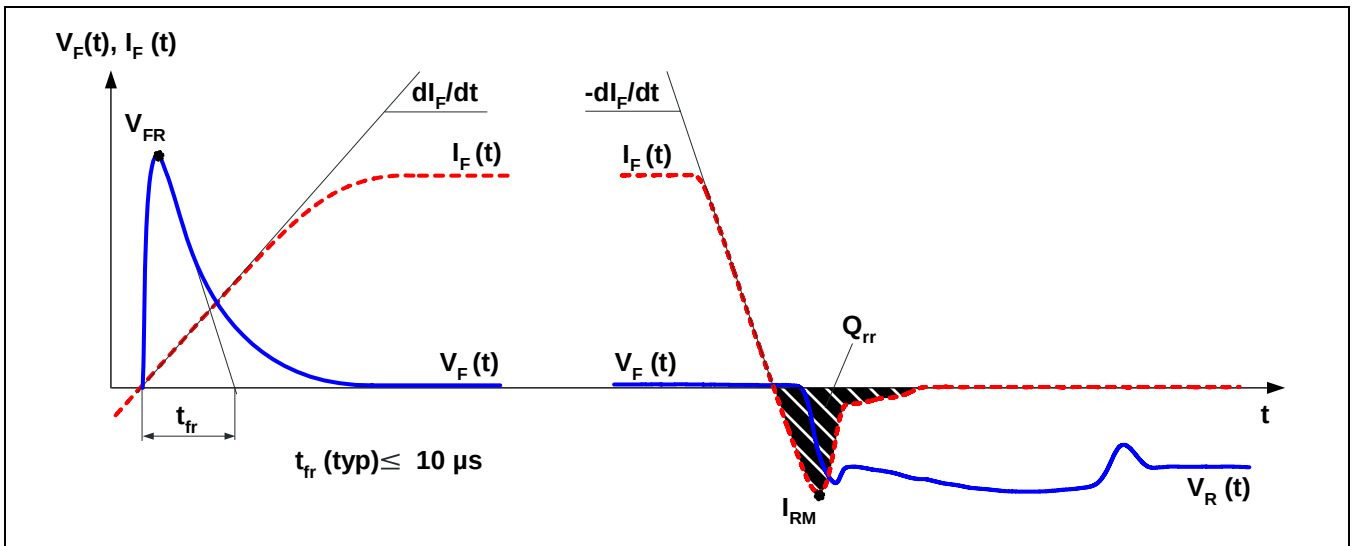


Fig. 6 General current and voltage waveforms

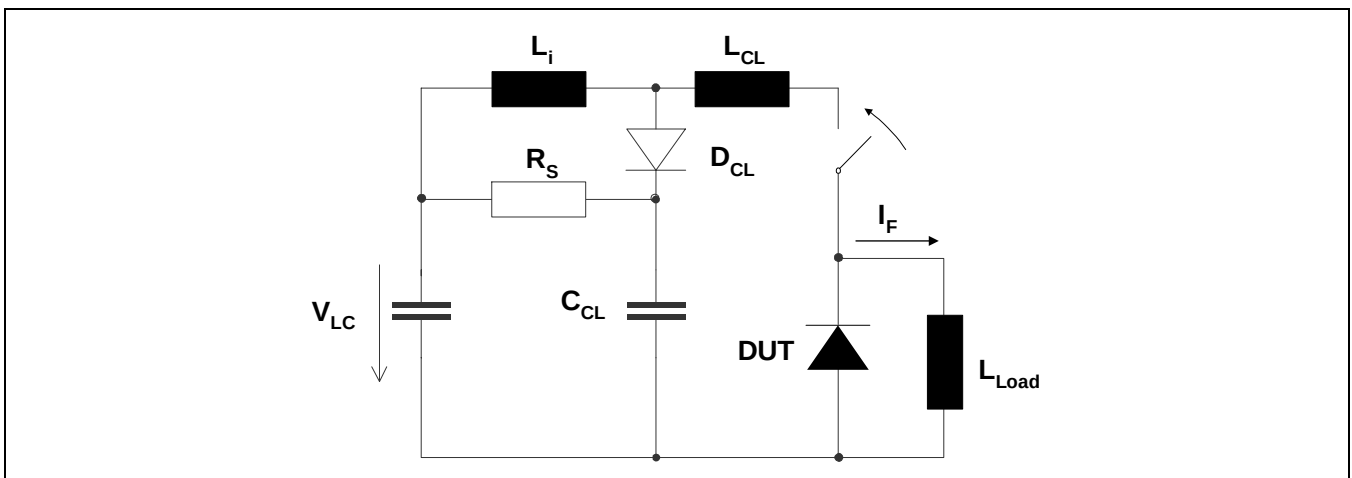


Fig. 7 Test circuit.

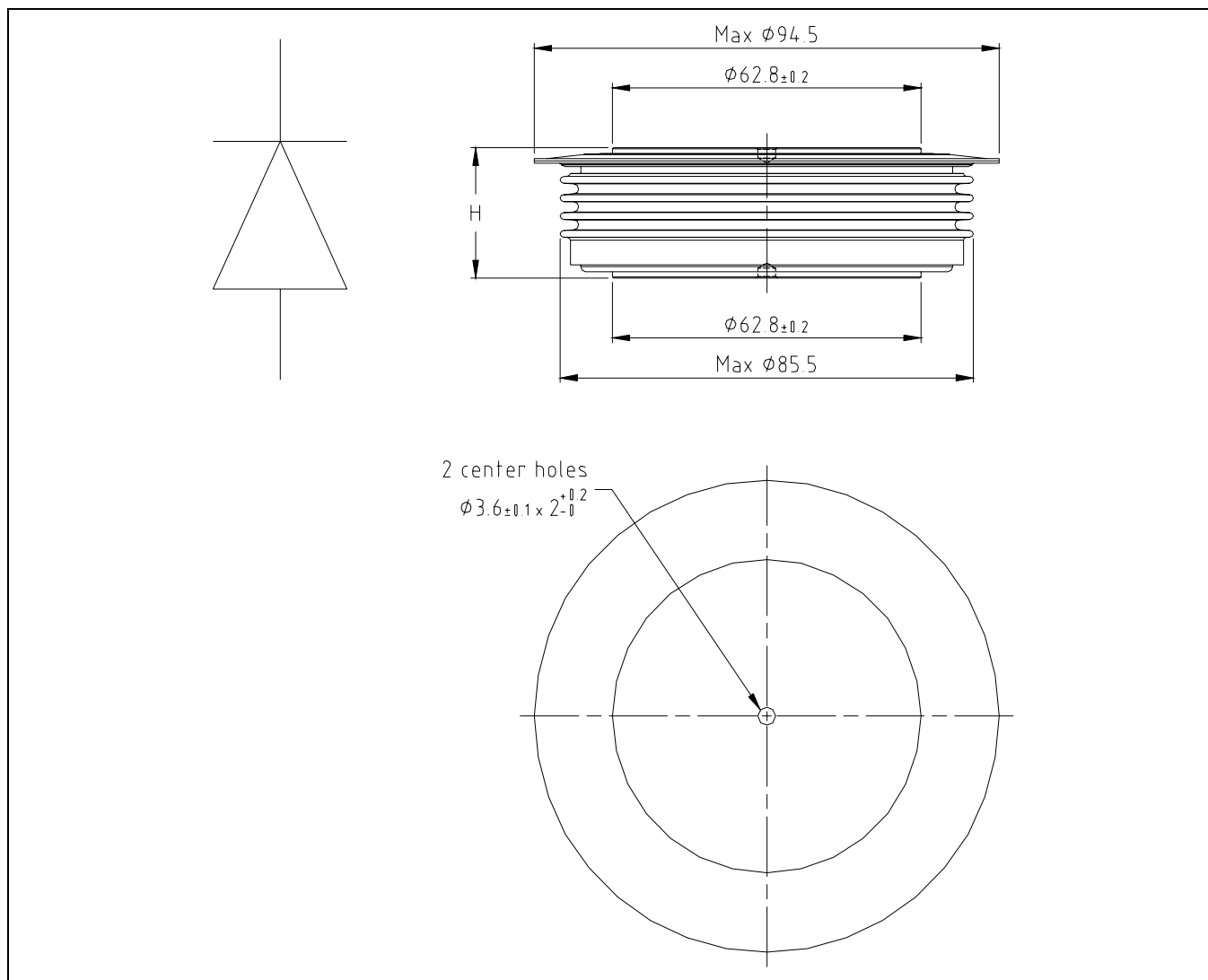


Fig. 8 Device Outline Drawing

Related documents:

Doc. Nr.	Title
5SYA 2036	Recommendations regarding mechanical clamping of Press Pack High Power Semiconductors
5SYA 2064	Applying Fast Recovery Diodes
5SZK 9104	Specification of environmental class for pressure contact diodes, PCTs and GTO, STORAGE
5SZK 9105	Specification of environmental class for pressure contact diodes, PCTs and GTO, TRANSPORTATION
5SZK 9115	Specification of environmental class for presspack Diodes, PCTs and GTOs, OPERATION (Industry)
5SZK 9116	Specification of environmental class for presspack Diodes, PCTs and GTOs, OPERATION (Traction)

Please refer to <http://www.abb.com/semiconductors> for current version of documents.

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